

N-Channel Enhancement Mode Power MOSFET

General Description

The HN0801 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for power switching application and LED backlighting.

Application

- Power switching application
- LED backlighting

Features

- $V_{DS} = 100V, I_D = 8A$
- $R_{DS(ON)} < 95m \quad @ \quad V_{GS}=4.5V$
- $R_{DS(ON)} < 85m \quad @ \quad V_{GS}=10V$
- Ultra Low On-Resistance
- High UIS and UIS 100% Test

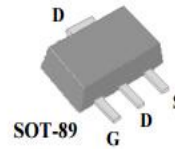
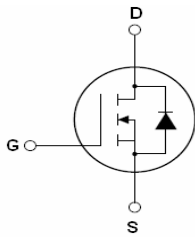


Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	100	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
$I_{D(DC)}$	Drain Current (DC) at $T_c=25^\circ C$	8	A
$I_{D(DC)}$	Drain Current (DC) at $T_c=100^\circ C$	6.5	A
$I_{DM(pulse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	56	A
P_D	Maximum Power Dissipation($T_c=25^\circ C$)	28	W
E_{AS}	Single Pulse Avalanche Energy (Note 2)	16	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	$^\circ C$

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.EAS condition: $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25 \Omega$

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3.3	$^{\circ}C/W$

Table 3. Electrical Characteristics (TA=25 $^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100			V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25 $^{\circ}C$)	$V_{DS}=100V, V_{GS}=0V$			1	μA
I_{DSS}	Zero Gate Voltage Drain Current(Tc=100 $^{\circ}C$)	$V_{DS}=100V, V_{GS}=0V$			5	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.5	2.0	2.6	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=10V, I_D=4.5A$		85	95	m Ω
Dynamic Characteristics						
g_{FS}	Forward Transconductance	$V_{DS}=5V, I_D=4.5A$	5			S
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V$ $f=1.0MHz$		612		PF
C_{oss}	Output Capacitance			120		PF
C_{rss}	Reverse Transfer Capacitance			91		PF
Q_g	Total Gate Charge	$V_{DS}=50V, I_D=4.5A$ $V_{GS}=10V$		11		nC
Q_{gs}	Gate-Source Charge			1.9		nC
Q_{gd}	Gate-Drain Charge			2.8		nC
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=50V, R_L=8.6\Omega$ $V_{GS}=10V, R_G=3\Omega$		8		nS
t_r	Turn-on Rise Time			3		nS
$t_{d(off)}$	Turn-Off Delay Time			17		nS
t_f	Turn-Off Fall Time			4.5		nS
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current(Body Diode)			14		A
I_{SDM}	Pulsed Source-Drain Current(Body Diode)			56		A
V_{SD}	Forward On Voltage ^(Note 1)	$T_J=25^{\circ}C, I_{SD}=1A, V_{GS}=0V$		0.74	1	V
t_{rr}	Reverse Recovery Time ^(Note 1)	$T_J=25^{\circ}C, I_F=4.5A$ $di/dt=500A/\mu s$		21		nS
Q_{rr}	Reverse Recovery Charge ^(Note 1)				97	
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L_S+L_D)				

Notes 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1.5\%$, Starting $T_J=25^{\circ}C$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. On-Region Characteristics

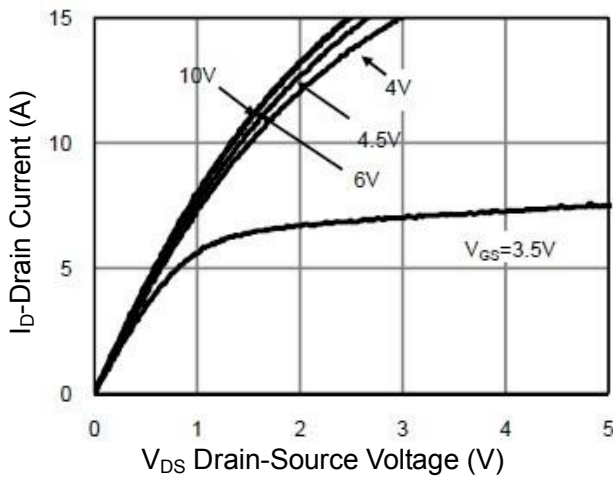


Figure 2: Transfer Characteristics

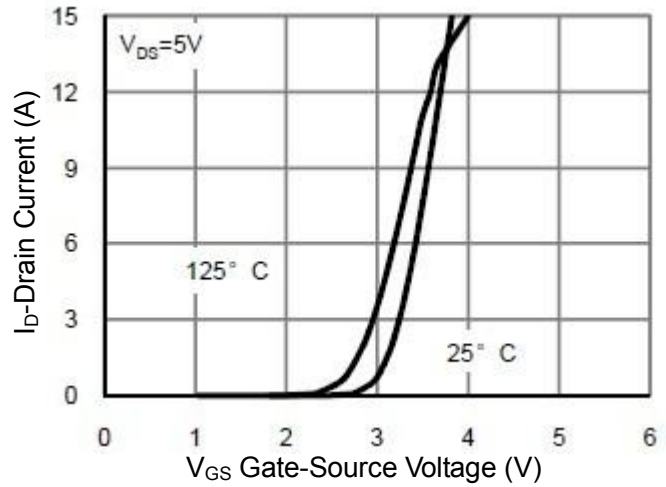


Figure3. On-Resistance vs. Drain Current and Gate Voltage

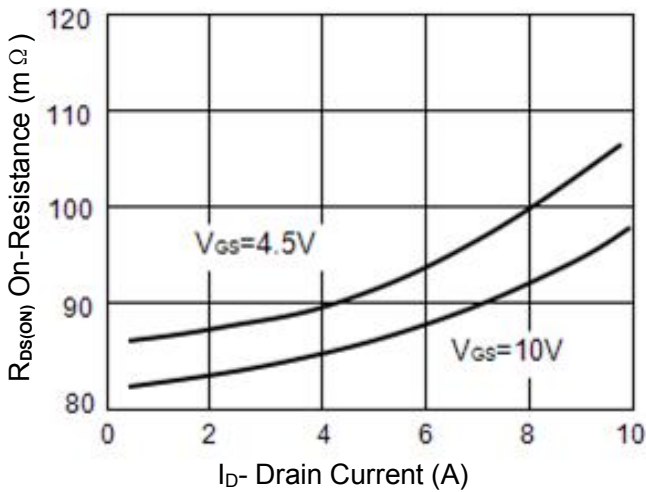


Figure4. On-Resistance vs. Junction Temperature

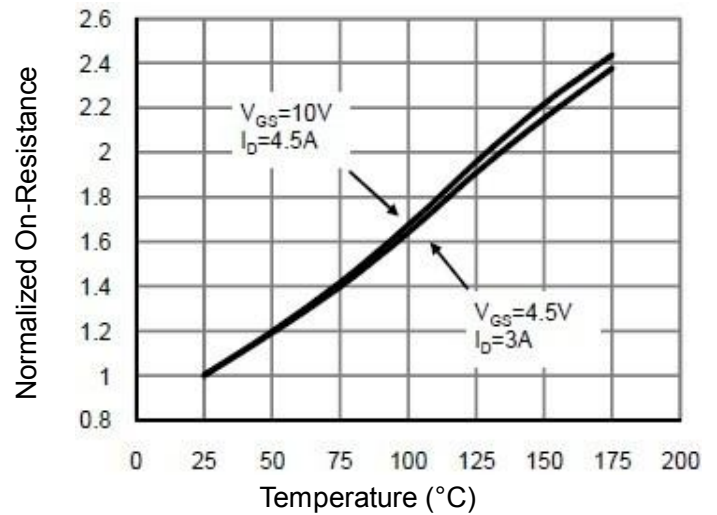


Figure5. On-Resistance vs. Gate-Source Voltage

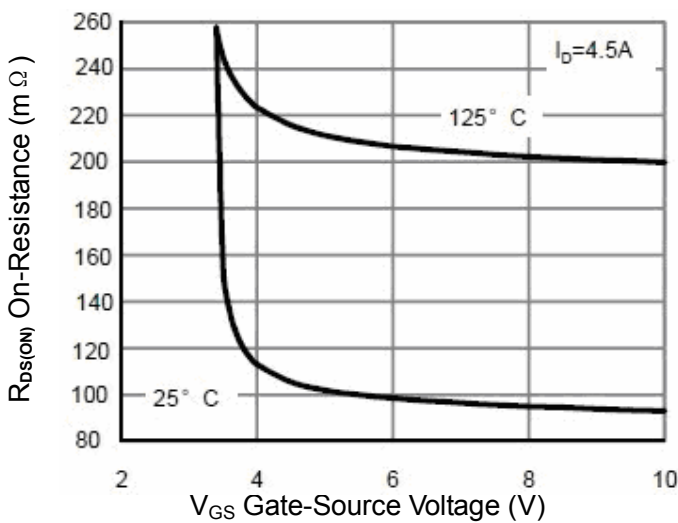


Figure6. Body-Diode Characteristics

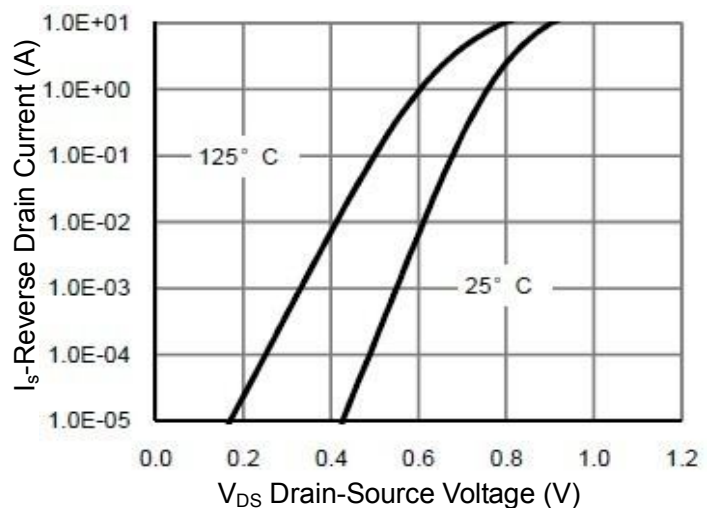




Figure 7. Gate-Charge Characteristics

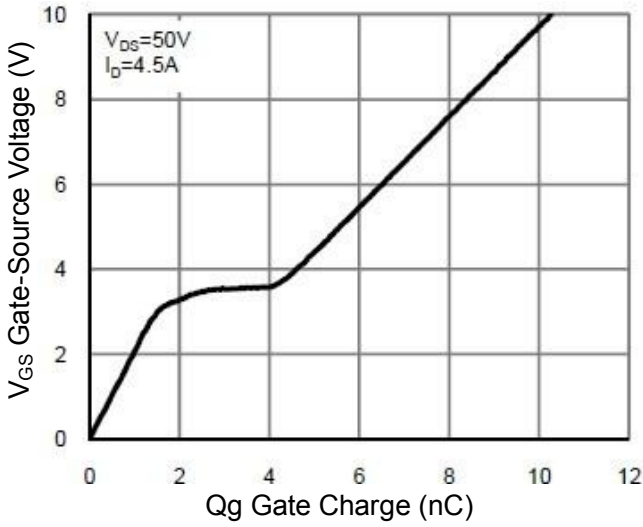


Figure 8. Capacitance Characteristics

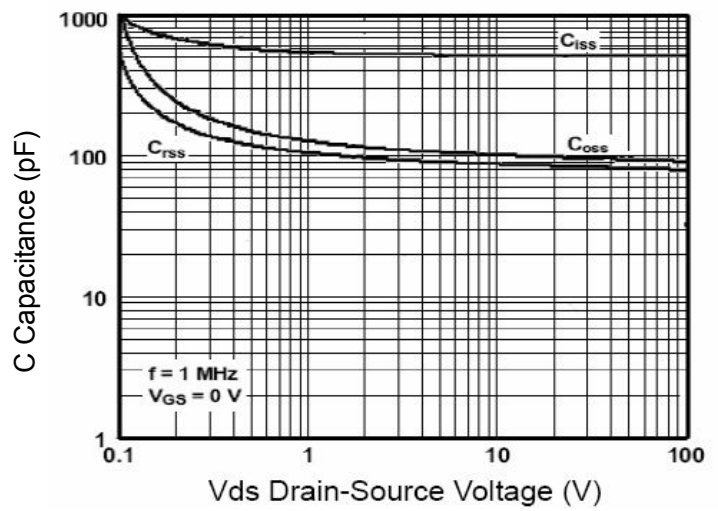


Figure 9. Maximum Forward Biased Safe Operating Area

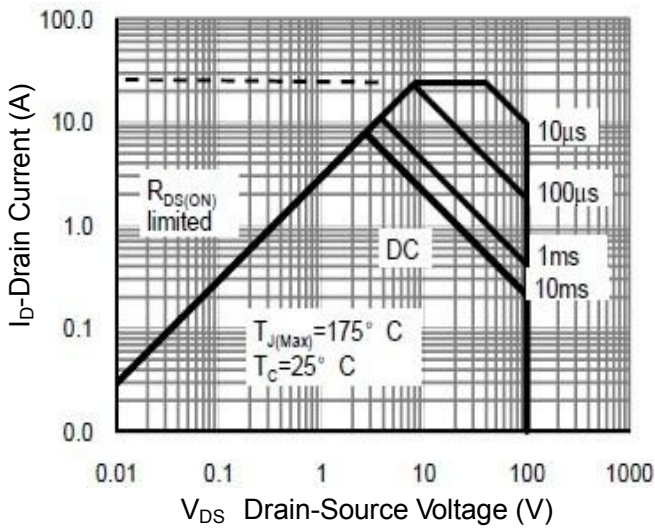


Figure 10. Single Pulse Power Rating Junction-to-Case

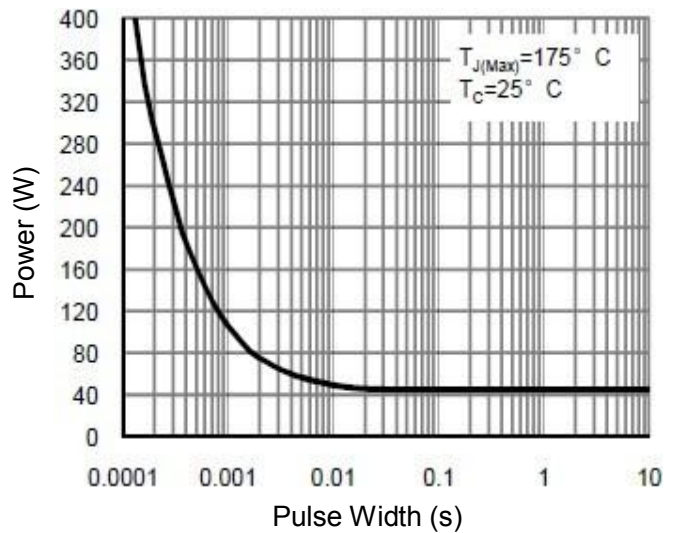


Figure 11. Normalized Maximum Transient Thermal Impedance

